

N-Channel 100V (D-S) Power MOSFET

Features

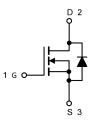
- 100% Avalanche Tested
- Extremely Low Losses with Low FOM Rdson*Qg
- Halogen Free, Pb-Free
- RoHS Compliant



TO-252 (D-PAK)

Applications

- DC/DC
- Motors, lamps
- Power switching



Absolute Maximum Ratings (TJ=25°C unless otherwise noted)						
Parameter		Symbol	Value	Unit		
Drain Source Voltage		V _{DS}	100	V		
Gate Source Voltage		V_{GS}	±20	V		
Drain Current, Continuous V _{GS} =10V (<i>Note 1</i>)	T _C =25°C	l _D	140	А		
	T _C =100°C	טו	85			
Drain Current, Pulsed (Note 2)		I _{DM}	417	А		
Power Dissipation (Note 3)	T _C =25°C	P _D	272	W		
Operating Junction/ Storage Temperature Range		T _J / T _{STG} -55 to +150		°C		

Note 1: Calculated continuous current based on maximum allowable junction temperature.

Thermal Resistance					
Parameter	Symbol	Max	Unit		
Junction-to-case (Note 3)	R _{θJC}	0.46	°C/W		

Note 3: The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

Note 2: Repetitive rating; pulse width limited by max. junction temperature.



Electrical Characteristics (T _J =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250µA	100			V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =100V, V _{GS} =0V			1	uA
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250uA	2		4	V
Gate Leakage Current	I _{GSS}	V _{GS} =±20V,VDS=0V			±100	nA
Drain-Source On-state Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		4.3	6	mΩ
Total Gate Charge	Qg	V _{GS} =10V, V _{DS} =50V, I _D =20A		43		
Gate-Source Charge	Q _{gs}			10		nC
Gate-Drain Charge	Q_{gd}			9		
Turn-on Delay Time	t _{d(on)}	V_{GS} =10V, V_{DS} =50V, I_D =20A, R_{GEN} =3 Ω		14		
Turn-on Rise Time	t _r			26		
Turn-off Delay Time	$t_{\sf d(off)}$			44		ns
Turn-off Fall Time	t _f			38		
Input Capacitance	C _{iss}	V _{GS=} 0V, V _{DS} =50V, f=1MHz		4650		
Output Capacitance	C _{oss}			607		pF
Reverse Transfer Capacitance	C _{rss}			19.7		

Reverse Diode Characteristics (T _J =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Continuous Source Current (Body Diode)	Is	T _C =25°C			167	Α
Pulsed Source Current (Body Diode)	I _{SM}			1	417	
Diode Forward Voltage (Note 4)	V _{SD}	I _S =20A, V _{GS} =0V			1.2	V
Reverse Recovery Time	T _{rr}	T _C =25°C, I _F =20A, di/dt = 100 A/μs		60		ns
Reverse Recovery Charge	Qrr			61		nC





Typical Characteristics Curves (T_J = 25°C unless otherwise noted)

Fig.1 - Typical Output Characteristics

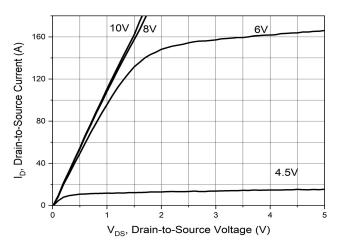


Fig.3 - RDS(on) vs. Junction Temperature

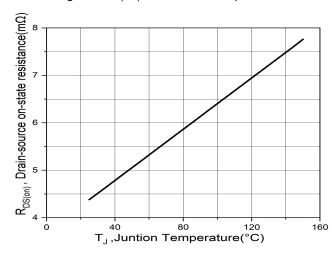


Fig.5 - Capacitance

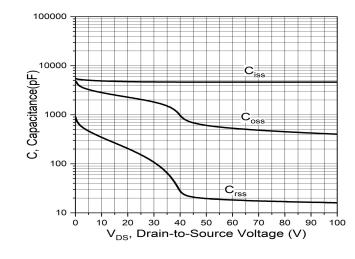


Fig.2 - Drain-to-Source Breakdown Voltage vs. Junction Temperature

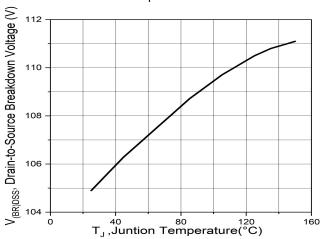


Fig.4 - Vth vs. Junction Temperature

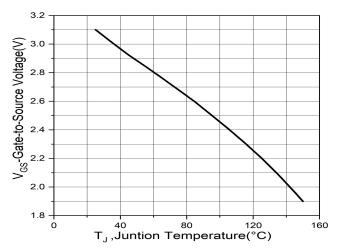
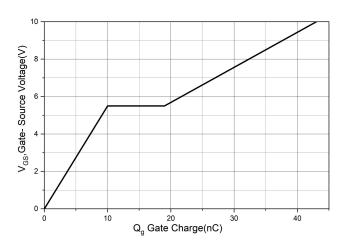


Fig.6 - Gate Charge





Typical Characteristics Curves (T_J = 25°C unless otherwise noted)

Fig.7 - Transfer Characteristics

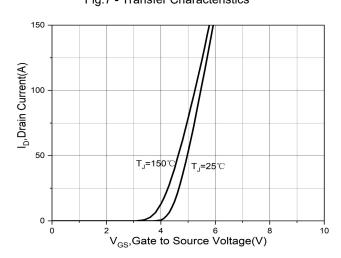
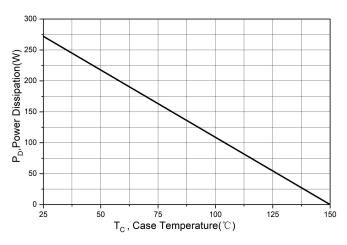


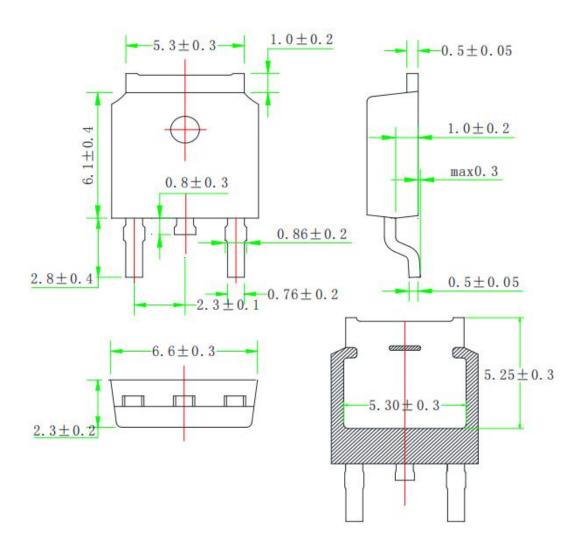
Fig.8 - Power Dissipation





Package Outline Dimensions (Unit: millimeters)

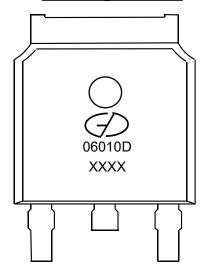
TO-252(D-PAK)







Marking Outline



Part Name: GMN06010D

1. Logo Mark:

2. P/N Mark: 06010D

3. Date Code: XXXX



GOOD-ARK Flectronics

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